

Patent

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Docket No.: 12405-US-PA-0P

Application No.: 10/711,509

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Applicant : Luo et al.

Application No. : 10/711,509

Filed : 2004/9/23

For : THIN FILM TRANSISTOR AND MANUFACTURING  
METHOD THEREOF

Art Unit : 2823

Examiner : Brewster, William M.

Response to Examiner's Amendment

002-1-571-273-8300

(Via fax: 1 page)

Examiner Brewster,

The Applicant agrees with your proposed amendment regarding the dopant concentration. The Applicant, however, disagrees with the proposed amendment regarding the deposition rate since the deposition rates for the first and second amorphous silicon sublayer can vary. In other words, the first deposition rate is not necessary lower than the second deposition rate. The Applicant believes the dopant concentration limitation already defines the claims over the prior art references.

If necessary, we can discuss in detail regarding the abovementioned issues via a telephonic interview.

Respectfully Submitted,

JIANQ CHYUN Intellectual Property Office

Date: Jan 4, 2006By: Belinda Lee  
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